NXP ACTT8-800C0 Thyristor datasheet

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AC Thyristor Triac power switch in a SOT78 (TO-220AB) plastic package with selfprotective clamping capabilities against low and high energy transients.

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Product data sheet

1. General description

AC Thyristor Triac power switch in a SOT78 (TO-220AB) plastic package with self-protective clamping capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High minimum I_{GT} for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	80	А
T _j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	8	А
V _{PP}	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; Fig. 6	-	-	2	kV





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AC Thyristor Triac power switch

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT} gate trigger current	gate trigger current	V_D = 12 V; I_T = 100 mA; LD+ G+; T_j = 25 °C; <u>Fig. 8</u>	5	-	30	mA
	V_D = 12 V; I_T = 100 mA; LD+ G-; T_j = 25 °C; <u>Fig. 8</u>	5	-	30	mA	
		V_D = 12 V; I_T = 100 mA; LD- G-; T_j = 25 °C; <u>Fig. 8</u>	5	-	30	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms

5. Pinning information

Table 2. Pinning information

1 CM common 2 LD load 3 G gate mb LD mounting base; load	ymbol
3 G gate	LD I
	G
mb LD mounting base; load	CM
TO-220AB (SOT78)	003aaf296

6. Ordering information

Table 3. Ordering information

	9					
Type number	ber Package					
	Name	Description	Version			
ACTT8-800C0	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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7. Marking

Table 4. Marking codes

Type number	Marking code
ACTT8-800C0	ACTT8-800C0

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3	-	8	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	80	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	88	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	32	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

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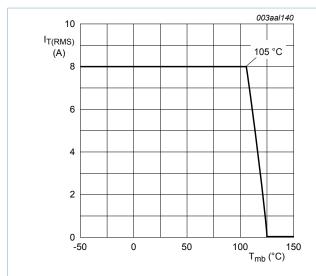


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

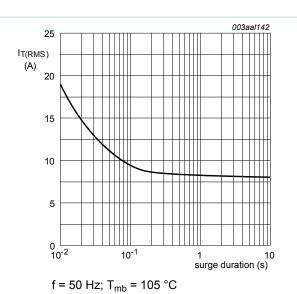
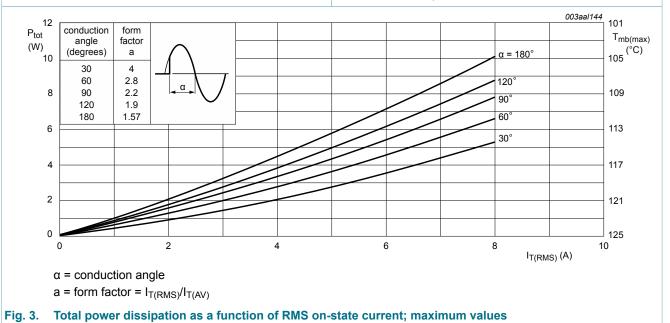


Fig. 2. RMS on-state current as a function of surge duration; maximum values



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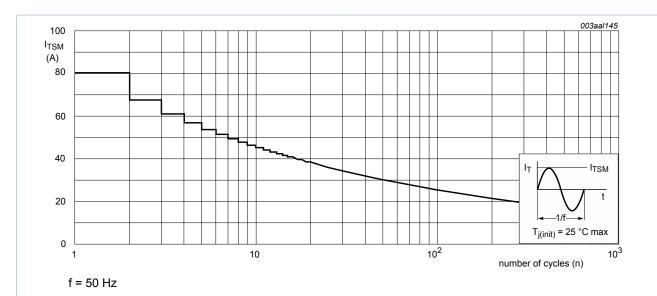


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

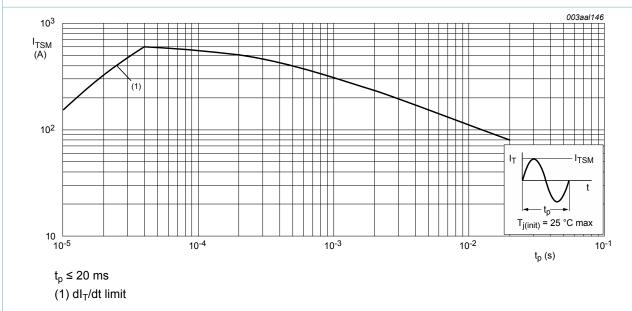
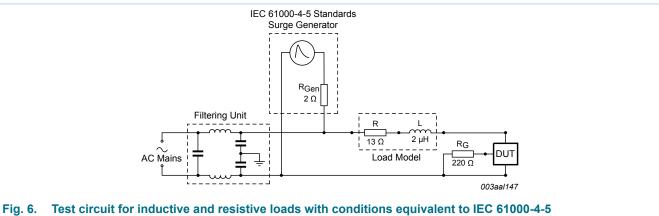


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 7	-	-	2	K/W
from junction to mounting base	half cycle; Fig. 7	-	-	2.4	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

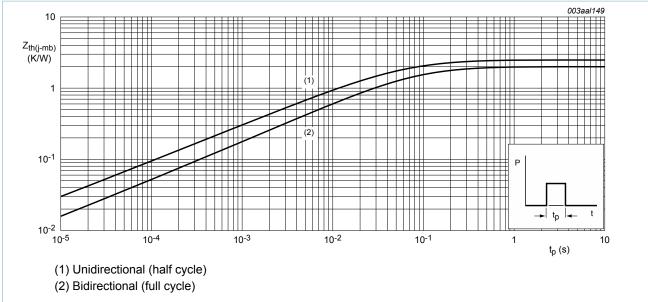


Fig. 7. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Static characteristics								
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	5	-	30	mA		
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	5	-	30	mA		
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 8$	5	-	30	mA		
IL	latching current	V_D = 12 V; I_G = 100 mA; LD+ G+; T_j = 25 °C; <u>Fig. 9</u>	-	-	50	mA		

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	70	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	35	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 100 \text{ mA}; T_j = 125 \text{ °C};$ Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μΑ
		V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic cl	haracteristics				-1	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms

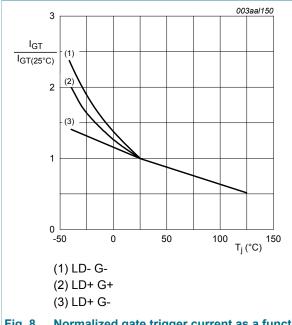


Fig. 8. Normalized gate trigger current as a function of junction temperature

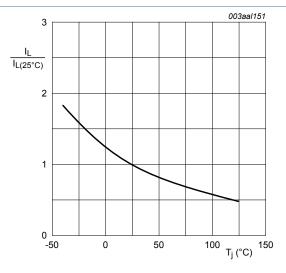


Fig. 9. Normalized latching current as a function of junction temperature

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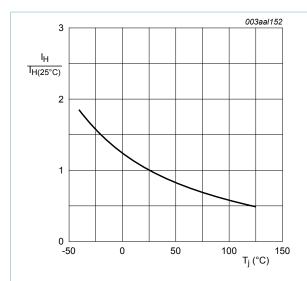
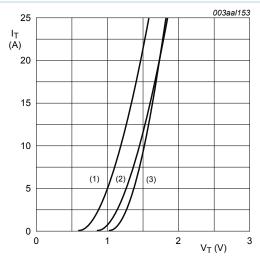


Fig. 10. Normalized holding current as a function of junction temperature



 $V_o = 1.103 \text{ V}; R_s = 0.034 \Omega$

(1) $T_j = 125$ °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

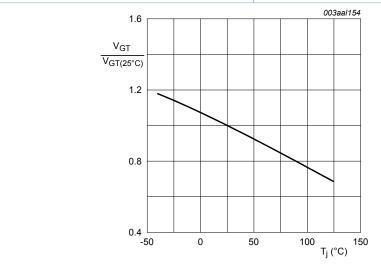


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

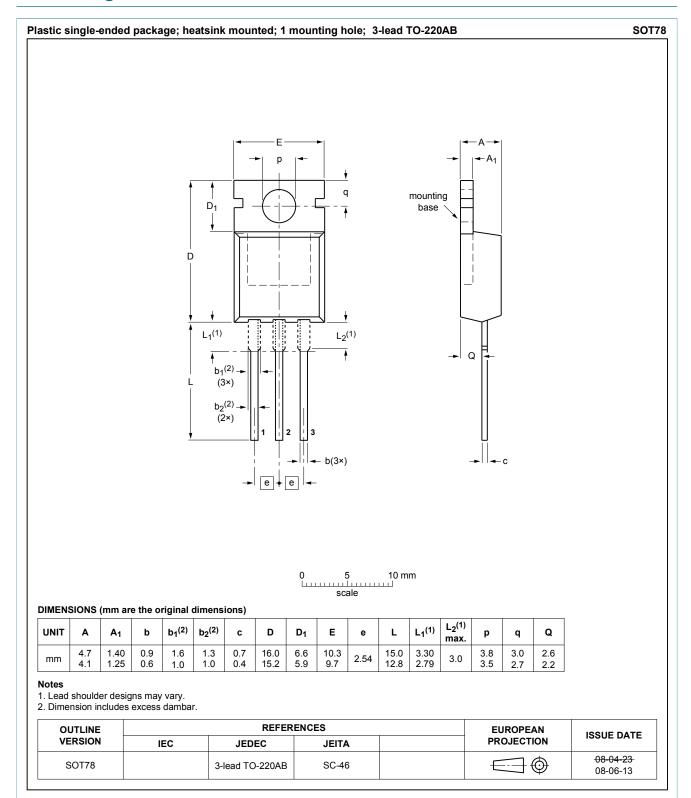


Fig. 13. Package outline TO-220AB (SOT78)

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